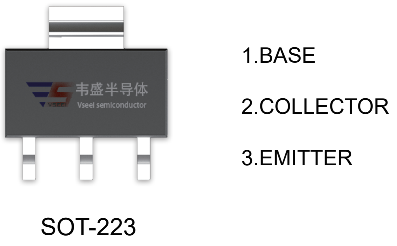
CZT32C TRANSISTOR (PNP)



FEATURES

- Complementary to CZT31C
- Power amplifier applications up to 3.0 amps.

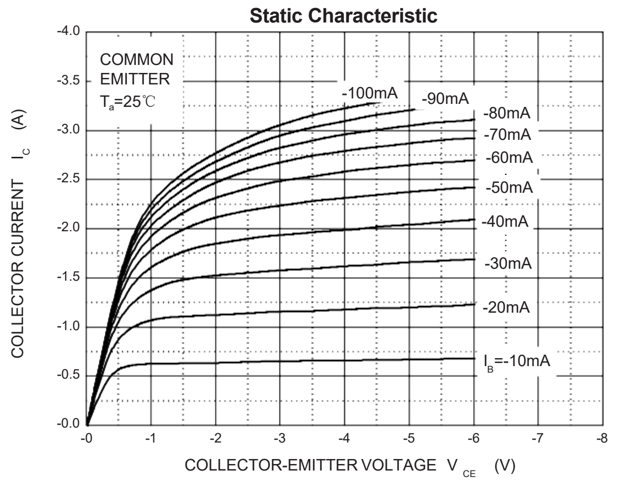
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

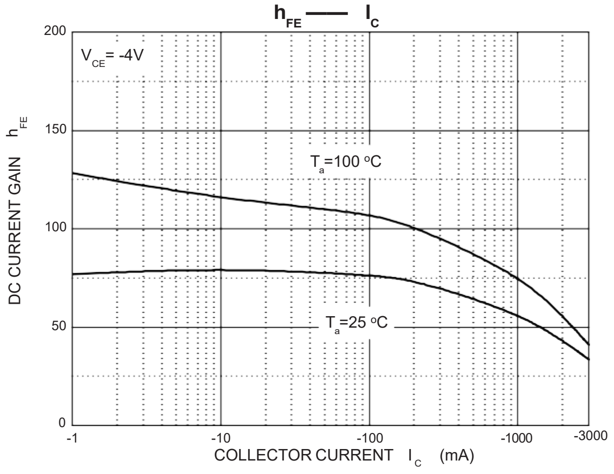
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	1	W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~150	℃

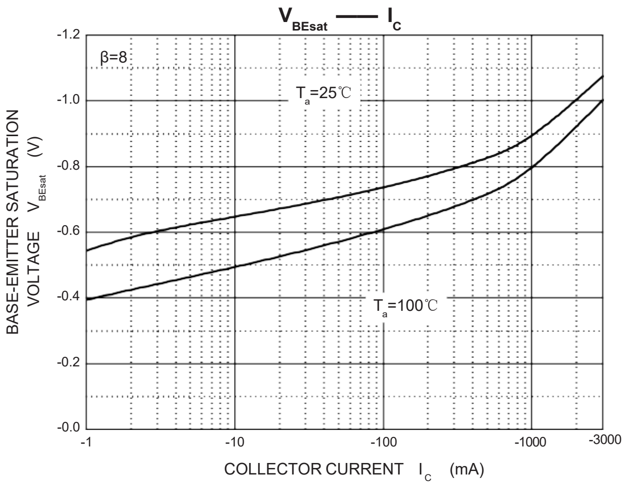
ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

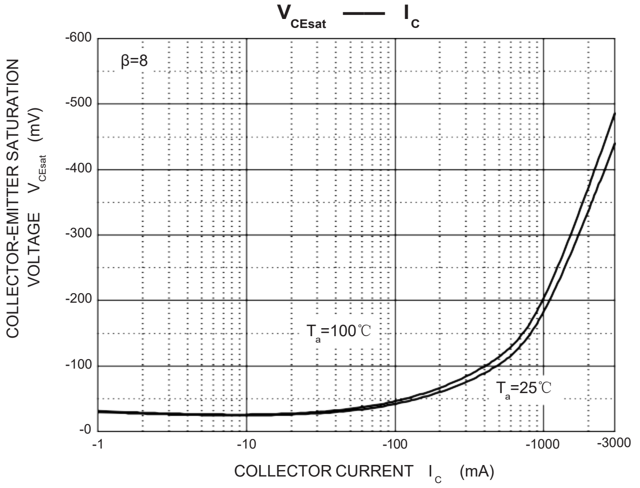
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1m A,I_E=0	-100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-30mA,I_B=0	-100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-3mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-100V,I_E=0			-200	uA
Base cut-off current	I_{CEO}	V_{CE}=-60V,I_B=0			-300	uA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-1	mA
DC current gain	$h_{FE(1)}$*	V_{CE}=-4V,I_C=-1A	25			
	$h_{FE(2)}$ *	V_{CE}=-4V,I_C=-3A	10		100	
Collector-emitter saturation voltage	$V_{CE(sat)}$ *	I_C=-3.0A,I_B=-375mA			-1.2	V
Base-emitter voltage	$V_{BE(on)}$ *	V_{CE}=-4V,I_C=-3A			-1.8	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-500mA,f=1MHz	3			MHz

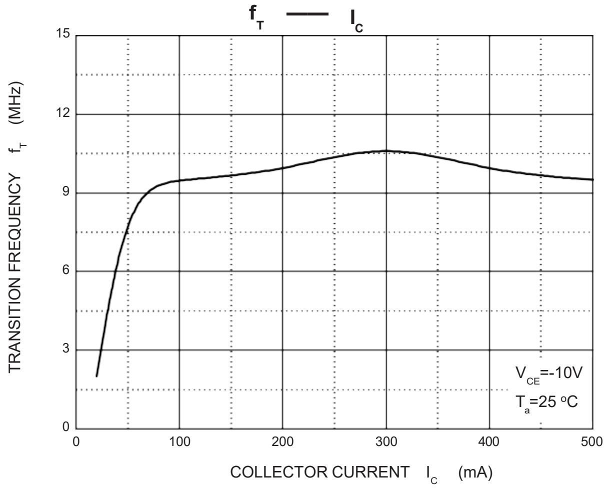
*** Pulsed , 2%D.C.**

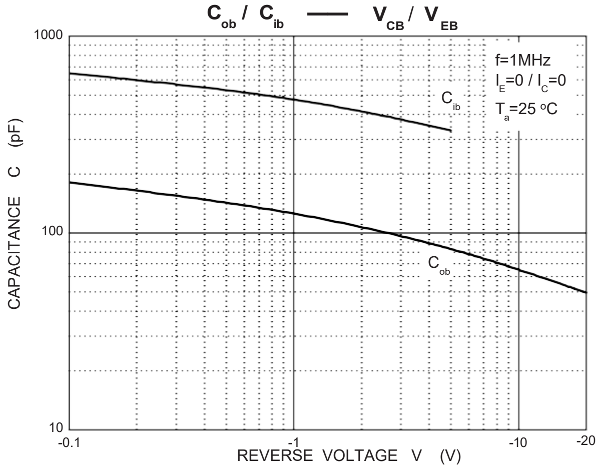

Static Characteristic

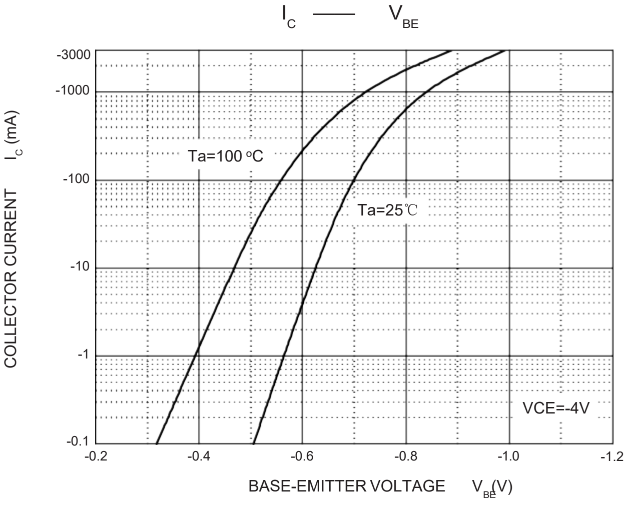

h_{FE} —— I_C

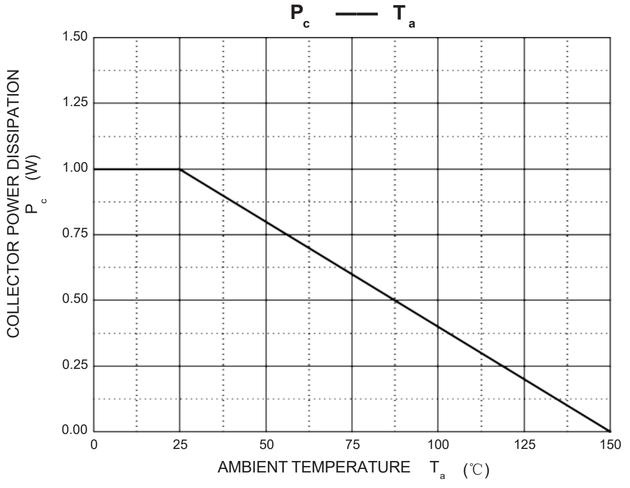

V_{BEsat} —— I_C


V_{CEsat} —— I_C


f_T —— I_C


C_{ob} / C_{ib} —— V_{CB} / V_{EB}


I_C —— V_{BE}


P_c —— T_a